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# FSEZ1216B Primary-Side-Regulation PWM Integrated Power MOSFET

#### **Features**

- Constant-Voltage (CV) and Constant-Current (CC) Control without Secondary-Feedback Circuitry
- Green-Mode Function: PWM Frequency Linearly Decreasing
- Fixed PWM Frequency at 50kHz with Frequency Hopping to Solve EMI Problems
- Cable Compensation in CV mode
- Low Startup Current: 10µA
- Low Operating Current: 3.5mA
- Peak-Current-Mode Control in CV Mode
- Cycle-by-Cycle Current Limiting
- V<sub>DD</sub> Over-Voltage Protection (OVP) with Auto-Restart
- V<sub>DD</sub> Under-Voltage Lockout (UVLO)
- Fixed Over-Temperature Protection (OTP) with Latch
- DIP-8 Package Available

### Applications

- Battery Chargers for Cellular Phones, Cordless Phones, PDA, Digital Cameras, Power Tools
- Best Choice to Replace Linear Transformer and RCC SMPS

#### Description

This highly integrated PWM controller provides several features to enhance the performance of low-power flyback converters. The proprietary topology enables most simplified circuit design especially for battery charger applications. A low-cost, smaller, and lighter charger results when compared to a conventional design or a linear transformer. The startup current is only  $10\mu$ A, which allows large startup resistance for further power saving.

To minimize the standby-power consumption, the proprietary green-mode function provides off-time modulation to linearly decrease PWM frequency under light-load conditions. This green-mode function assists the power supply in meeting power conservation requirements.

By using FSEZ1216B, a charger can be implemented with few external components and minimized cost. A typical output CV/CC characteristic envelope is shown in Figure 1.

FSEZ1216B series controllers are available in an 8-pin DIP package.



Figure 1. Typical Output V-I Characteristic

### **Ordering Information**

Part Numb	er	Operating Temperature Range	Eco Status	Package	Packing Method
FSEZ1216B	NY	-40°C to +105°C	Green	Green 8-Lead, Dual Inline Package (DIP-8)	

Ø For Fairchild's definition of "green" Eco Status, please visit: <u>http://www.fairchildsemi.com/company/green/rohs\_green.html</u>.



FSEZ1216B — Primary-Side-Regulation PWM Integrated Power MOSFET



# **Pin Definitions**

Pin #	Name	Description
1	CS	Analog Input, Current Sense. Connected to a current-sense resistor for peak-current-mode control in CV mode. The current-sense signal is also provided for output-current regulation in CC mode.
2	COMR	Analog Output, Cable Compensation. Connect a resistor between COMR and GND for cable loss compensation in CV mode.
3	СОМІ	Analog Output, Current Compensation. Output of the current error amplifier. Connect a capacitor between COMI pin and GND for frequency compensation.
4	COMV	Analog Output, Voltage Compensation. Output of the voltage error amplifier. Connect a capacitor between COMV pin and GND for frequency compensation.
5	VS	Analog Input, Voltage Sense. Output-voltage-sense input for output-voltage regulation.
6	VDD	Supply, Power Supply.
7	GND	Voltage Reference, Ground.
8	DRAIN	Driver Output, Power MOSFET Drain. This pin is the high-voltage power MOSFET drain

**Absolute Maximum Ratings** 

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Min.	Max.	Unit	
V <sub>VDD</sub>	DC Supply Voltage <sup>(1,2)</sup>			30	V
V <sub>VS</sub>	VS Pin Input Voltage	VS Pin Input Voltage		7.0	V
V <sub>CS</sub>	CS Pin Input Voltage		-0.3	7.0	V
V <sub>COMV</sub>	Voltage-Error Amplifier Output Voltage		-0.3	7.0	V
V <sub>COMI</sub>	Voltage-Error Amplifier Output Voltage		-0.3	7.0	V
V <sub>DS</sub>	Drain-Source Voltage			600	V
	Continuous Drain Current	T <sub>C</sub> =25°C		1	А
ID	Continuous Drain Current	T <sub>C</sub> =100°C		0.6	А
I <sub>DM</sub>	Pulsed Drain Current			4	А
E <sub>AS</sub>	Single-Pulse Avalanche Energy			33	mJ
I <sub>AR</sub>	Avalanche Current			1	А
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> <50°C)			800	mW
$R_{ heta JA}$	Thermal Resistance (Junction-to-Air)			113	°C/W
$R_{\theta JC}$	Thermal Resistance (Junction-to-Case)	)		67	°C/W
TJ	Operating Junction Temperature			+150	°C
T <sub>STG</sub>	Storage Temperature Range		-55	+150	°C
TL	Lead Temperature (Wave Soldering or	IR, 10 Seconds)		+260	°C
ESD	Electrostatic Discharge Capability, Human Body Model, JEDEC: JESD22-A114			3.0	KV
ESD	Electrostatic Discharge Capability, Cha Model, JEDEC: JESD22-C101	Electrostatic Discharge Capability, Charged Device Model, JEDEC: JESD22-C101		1000	V

Notes:

1. Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device.

2. All voltage values, except differential voltages, are given with respect to GND pin.

# **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Тур.	Max.	Unit
T <sub>A</sub>	Operating Ambient Temperature	-40		+105	°C

 $V_{DD}$ =15V, T<sub>A</sub>=25°C, unless otherwise specified.

Symbol	Par	ameter	Conditions	Min.	Тур.	Max.	Units
VDD SECT	ION				L		
V <sub>OP</sub>	Continuously Operating Voltage					25	V
$V_{\text{DD-ON}}$	Turn-On Threshold Voltage			15	16	17	V
V <sub>DD-OFF</sub>	Turn-Off Three	shold Voltage		4.5	5.0	5.5	V
I <sub>DD-ST</sub>	Startup Currer	nt	0 <v<sub>DD<v<sub>DD-ON-0.16V</v<sub></v<sub>		10	20	μA
I <sub>DD-OP</sub>	Operating Current		$V_{DD}$ =20V, f <sub>S</sub> =f <sub>OSC</sub> , V <sub>VS</sub> =2V, V <sub>CS</sub> =3V, C <sub>L</sub> =1nF		3.5	5.0	mA
I <sub>DD-GREEN</sub>	Green-Mode Operating Supply Current		$\label{eq:VDD} \begin{array}{l} V_{DD} = 20V, \ V_{VS} = 2.7V \\ V_{CS} = 0V, \ V_{COMV} = 0V \\ f_{S} = f_{OSC-N-MIN}, \ C_L = 1nF \end{array}$		1	2	mA
V <sub>DD-OVP</sub>	V <sub>DD</sub> Over-Voltage-Protection Level		$V_{VS}$ =2.3V, $V_{CS}$ =3V	27	28	29	V
t <sub>D-VDDOVP</sub>	V <sub>DD</sub> Over-Voltage-Protection Debounce Time		f <sub>S</sub> =f <sub>OSC</sub> , V <sub>VS</sub> =2.3V	100	250	400	μs
OSCILLAT	OR SECTION						
£	Frequency	Center Frequency	T <sub>A</sub> =25°C, V <sub>VS</sub> =2.3V	48	50	55	KHz
f <sub>OSC</sub>		Frequency- Hopping Range	$V_{CS}$ =1.5V, $V_{VS}$ =2V	±1.0	±1.5	±2.3	
t <sub>FHR</sub>	Frequency-Ho	pping Period	V <sub>CS</sub> =1.5V, V <sub>VS</sub> =2V		2.56		ms
f <sub>OSC-N-MIN</sub>	Minimum Freq	uency at No-Load	$V_{VS}$ =2.7V, $V_{COMV}$ =0V		500		Hz
$f_{\text{OSC-CM-MIN}}$	Minimum Freq	uency at CCM	$V_{VS}$ =2.3V, $V_{CS}$ =0.5V		18		KHz
$\mathbf{f}_{DV}$	Frequency Va Deviation	riation vs. $V_{DD}$	$V_{DD}$ =10V to 25V			5	%
f <sub>DT</sub>	Frequency Variation vs. Temperature Deviation		T <sub>A</sub> =-40°C to 105°C			15	%
VOLTAGE-	SENSE SECT	ION					
Ivs-uvp	Sink Current for Protection	or Brownout	R <sub>VS</sub> =20KΩ		125		μA
I <sub>tc</sub>	IC Compensat	ion Bias Current			9.5		μA
V <sub>BIAS-COMV</sub>	Adaptive Bias Dominated by		V <sub>COMV</sub> =0V,R <sub>VS</sub> =20KΩ		1.4		V

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
CURRENT	-SENSE SECTION		1	1		
t <sub>PD</sub>	Propagation Delay to GATE Output			100	200	ns
t <sub>MIN-N</sub>	Minimum On-Time at No-Load	$V_{VS}$ =-0.8V, R <sub>CS</sub> =2K $\Omega$ V <sub>COMV</sub> =1V		1100		ns
t <sub>MINCC</sub>	Minimum On-Time in CC Mode	V <sub>VS</sub> =0V, V <sub>COMV</sub> =2V		400		ns
V <sub>TH</sub>	Threshold Voltage for Current Limit			1.3		V
VOLTAGE	-ERROR-AMPLIFIER SECTION	1				
V <sub>VR</sub>	Reference Voltage		2.475	2.500	2.525	V
V <sub>N</sub>	Green-Mode Starting Voltage on COMV Pin	f <sub>S</sub> =f <sub>OSC</sub> -2KHz V <sub>VS</sub> =2.3V		2.8		V
V <sub>G</sub>	Green-Mode Ending Voltage on COMV Pin	f <sub>S</sub> =1KHz		0.8		V
I <sub>V-SINK</sub>	Output Sink Current	V <sub>VS</sub> =3V, V <sub>COMV</sub> =2.5V		90		μA
IV-SOURCE	Output Source Current	V <sub>VS</sub> =2V, V <sub>COMV</sub> =2.5V		90		μA
V <sub>V-HGH</sub>	Output High Voltage	V <sub>VS</sub> =2.3V	4.5			V
CURRENT	-ERROR-AMPLIFIER SECTION	l				
VIR	Reference Voltage		2.475	2.500	2.525	V
I <sub>I-SINK</sub>	Output Sink Current	V <sub>CS</sub> =3V, V <sub>COMI</sub> =2.5V		55		μA
I <sub>I-SOURCE</sub>	Output Source Current	V <sub>CS</sub> =0V, V <sub>COMI</sub> =2.5V		55		μA
V <sub>I-HGH</sub>	Output High Voltage	V <sub>CS</sub> =0V	4.5			V
CABLE CO	MPENSATION SECTION					
V <sub>COMR</sub>	Variation Test Voltage on COMR pin for Cable Compensation	R <sub>COMR</sub> =100kΩ		0.85		V

# **Electrical Characteristics**

 $V_{DD}$ =15V,  $T_A$ =25°C, unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	
NTERNAL	NTERNAL MOSFET SECTION						
DCY <sub>MAX</sub>	Maximum Duty Cycle			75		%	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μΑ, V <sub>GS</sub> =0V	600			V	
$\Delta \text{BV}_{\text{DSS}}$ / $\Delta \text{T}_{\text{J}}$	Breakdown-Voltage Temperature Coefficient	$I_D$ =250µA, Referenced to 25°C		0.6		V/°C	
ls	Maximum Continuous Drain- Source Diode Forward Current				1	А	
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				4	А	
R <sub>DS(ON)</sub>	Static Drain-Source On- Resistance	I <sub>D</sub> =0.5A, V <sub>GS</sub> =10V		9.3	11.5	Ω	
		V <sub>DS</sub> =600V, V <sub>GS</sub> =0V T <sub>C</sub> =25°C			1	μA	
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =480V, V <sub>GS</sub> =0V T <sub>C</sub> =100°C			10	μA	
t <sub>D-ON</sub>	Turn-On Delay Time	$V_{DS}$ =300V, I <sub>D</sub> =1.1A R <sub>G</sub> =25 $\Omega^{(3,4)}$		7	24	ns	
tr	Rise Time			21	52	ns	
t <sub>D-OFF</sub>	Turn-off Delay Time			13	36	ns	
t <sub>f</sub>	Fall Time			27	64	ns	
C <sub>ISS</sub>	Input Capacitance	$V_{GS}$ =0V, $V_{DS}$ =25V f <sub>S</sub> =1MHz		130	170	pF	
C <sub>OSS</sub>	Output Capacitance			19	25	pF	
OVER-TEM	PERATURE-PROTECTION SE	ECTION					
T <sub>OTP</sub>	Threshold Temperature for OTP <sup>(5)</sup>			140		°C	

Notes:

3. Pulse Test: Pulse width  $\leq$  300µs, Duty cycle  $\leq$  2%.

4. Essentially independent of operating temperature.

5. When the OTP is activated, the power system enters latch mode and output is disabled.







# **Functional Description**

The proprietary topology of FSEZ1216B enables most simplified circuit design especially for battery charger applications. Without secondary feedback circuitry, the CV and CC control can still be achieved accurately. As shown in Figure 24, with the frequency-hopping, PWM operation, EMI problem can be solved by using minimized filter components. FSEZ1216B also provides many protection functions. The VDD pin is equipped with over-voltage protection (OVP) and under-voltage lockout (UVLO). Pulse-by-pulse current limiting and CC control ensure over-current protection (OCP) at heavy loads. The GATE output is clamped at 15V to protect the external MOSFET from over-voltage damage. Also, the internal over-temperature-protection (OTP) function shuts down the controller with latch when over heated.



Figure 24. Frequency Hopping

### Startup Current

The startup current is only 10µA. Low startup current allows a startup resistor with a high resistance and a low wattage to supply the starup power for the controller. A 1.5M $\Omega$ , 0.25W, startup resistor and a 10µF/25V V<sub>DD</sub> hold-up capacitor is sufficient for an AC-to-DC power adapter with a wide input range (100V<sub>AC</sub> to 240V<sub>AC</sub>).

### **Operating Current**

The operating current has been reduced to 3.5mA. The low operating current results in higher efficiency and reduces the V<sub>DD</sub> hold-up capacitance requirement. Once FSEZ1216B enters deep-green mode, the operating current is reduced to 1mA, assisting the power supply to easily meet the power conservation requirement.

### **Green-Mode Operation**

Figure 25 shows the characteristics of the PWM frequency vs. the output voltage of the error amplifier ( $V_{COMV}$ ). The FSEZ1216B uses the positive, proportional, output load parameter ( $V_{COMV}$ ) as an indication of the output load for modulating the PWM frequency. In heavy-load conditions, the PWM frequency is fixed at 50KHz. Once  $V_{COMV}$  is lower than  $V_N$ , the PWM frequency starts to linearly decrease from 50KHz to 500Hz, thus providing further power savings and easily meeting international power-conservation requirements.



Figure 25. Green-Mode Operation Frequency vs. V<sub>COMV</sub>

#### Constant Voltage (CV) and Constant Current (CC) Operation

An innovative technique of the FSEZ1216B can accurately achieve CV/CC characteristic output without secondary-side voltage or current-feedback circuitry. There is a feedback signal from the reflected voltage across the primary auxiliary winding for CV/CC operation. This voltage signal is proportional to secondary winding, so it provides the controller the feedback signal from secondary side and achieves constant-voltage-output property. In constant-currentoutput operation, this voltage signal is detected and examined by the precise constant-current-regulation controller, then determines the on-time of the MOSFET to control input power and provide constant-currentoutput property. With feedback voltage V<sub>CS</sub> across the current-sense resistor, the controller can obtain the input power of the power supply. Therefore, the region of constant-current-output operation can be adjusted by the current sense resistor.

### **Temperature Compensation**

The FSEZ1216B has built-in temperature compensation, in order to get better CV regulation at different ambient temperatures. This internal compensation current is a positive-temperature-coefficient (PTC) current that can compensate the forward-voltage drop of the secondary diode varying with temperature. This variation causes output-voltage rising at high temperature.

## Leading-Edge Blanking (LEB)

Each time the power MOSFET is switched on, a turn-on spike occurs at the sense resistor. To avoid premature termination of the switching pulse, a leading-edge blanking time is built in. Conventional RC filtering can therefore be omitted. During this blanking period, the current-limit comparator is disabled and it cannot switch off the gate driver.

#### Under-Voltage Lockout (UVLO)

The turn-on and turn-off thresholds of the FSEZ1216B are fixed internally at 16V/5V. During startup, the hold-up capacitor must be charged to 16V through the startup resistor, so that the FSEZ1216B is enabled. The hold-up capacitor continues to supply  $V_{DD}$  until power can be delivered from the auxiliary winding of the main transformer.  $V_{DD}$  must not drop below 5V during this startup process. This UVLO hysteresis window ensures that the hold-up capacitor is adequate to supply  $V_{DD}$  during startup.

### **V<sub>DD</sub> Over-Voltage Protection (OVP)**

 $V_{DD}$  OVP is built in to prevent damage due to overvoltage conditions. When the voltage  $V_{DD}$  exceeds 28V due to abnormal conditions, PWM pulses are disabled until the  $V_{DD}$  voltage drops below the UVLO and then startup again. Over-voltage conditions are usually caused by open feedback loops.

### **Over-Temperature Protection (OTP)**

The FSEZ1216B has a built-in temperature-sensing circuit to shut down PWM output once the junction temperature exceeds 140°C. While PWM output is shut down, the  $V_{DD}$  voltage gradually drops to the UVLO

voltage. Some of the FSEZ1216B's internal circuits are shut down, and  $V_{DD}$  gradually starts increasing again. When  $V_{DD}$  reaches 16V, all the internal circuits including the temperature-sensing circuit starts operating normally. If the junction temperature is still higher than 140°C, the PWM controller is shut down immediately.

#### **Built-In Slope Compensation**

The sensed voltage across the current-sense resistor is used for current-mode control and pulse-by-pulse current limiting. Built-in slope compensation improves stability and prevents sub-harmonic oscillations due to peak-current-mode control. The FSEZ1216B has a synchronized, positively-sloped ramp built-in at each switching cycle.

#### **Noise Immunity**

Noise from the current sense or the control signal can cause significant pulse-width jitter, particularly in continuous-conduction mode. While slope compensation helps alleviate these problems, further precautions should still be taken. Good placement and layout practices should be followed. Avoid long PCB traces and component leads, locating compensation and filter components near the FSEZ1216B.





#### BOM

Designator	Part Type	Designator	Part Type
D1, D2, D3, D4, D6	1N4007	R2	R 100KΩ
D5	SB560	R3	R 22Ω
D7	FR103	R4, R5	R 750KΩ
C1	1nF	R6	R 270Ω
C2	EC 1µF/400V	R7	R 137KΩ
C3	EC 10µF/400V	R8	R 510Ω
C5	4.7nF/1KV	R9	R 68KΩ
C6	EC 10µF/50V	R10	R 200KΩ
C7	EC 470µF/16V	R11	R 56KΩ
C8	EC 220µF/10	R12	R 1.3Ω
C9	1µF	R14	R 30Ω
C10	68nF	L4	1mH
C11	10nF	T1	EE16 (1.5mH)
C12 47pF		U1	IC FSEZ1216B
R1	R 18Ω		





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Datasheet Identification	Product Status	Definition
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